

Description

The HXY80P06NF uses advanced trench technology to provide excellent R_{DS(ON)}, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

DFN5X6-8L

General Features

 $V_{DS} = -60V I_{D} = -80A$

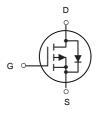
 $R_{DS(ON)}$ <3 m Ω V_{GS}=-10V

Application

Battery protection

Load switch

Uninterruptible power supply



P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
HXY80P06NF	DFN5X6-8L	HXY MOSFET	5000

Absolute Maximum Ratings (Tc=25 ℃ unless otherwise noted)

Symbol	Parameter	Rating	Units		
VDS	Drain-Source Voltage	Drain-Source Voltage -60			
Vgs	Gate-Source Voltage	±20	V		
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	-80	Α		
Ідм	Pulsed Drain Current ²	-280	А		
P _D @T _C =25°C	Total Power Dissipation ⁴	130	W		
Тѕтс	Storage Temperature Range	-55 to 150	°C		
TJ	Operating Junction Temperature Range	-55 to 150	°C		
Reja	Thermal Resistance Junction-Ambient ¹	62	°C/W		
Rejc	Thermal Resistance Junction-Case ¹	0.7	°C/W		



Electrical Characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Parameter Conditions		Тур	Max	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =-250μA	-60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-60V, V _{GS} =0V			-1	μA
Igss	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1 -2.0		-3.0	V
g FS	Forward Transconductance	V _{DS} =-5V, I _D =-15A		35		S
D.	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-15A		12	25	mΩ
RDS(ON)		V _{GS} =-4.5V, I _D =-10A		30	40	mΩ
Ciss	Input Capacitance			5604		pF
Coss	Output Capacitance	V _{DS} =-25V, V _{GS} =0V, f=1.0MHz		356		pF
Crss	Reverse Transfer Capacitance			265		pF
t _{d(on)}	Turn-on Delay Time			18		nS
t _r	Turn-on Rise Time			20		nS
t _{d(off)}	Turn-Off Delay Time	R_L =1.5Ω, R_{GEN} =3Ω		55		nS
t _f	Turn-Off Fall Time			35		nS
Qg	Total Gate Charge			62		nC
Q _{gs}	Gate-Source Charge	V _{GS} =-10V, V _{DS} =-30V, I _D =-20A		9.3		nC
Q_{gd}	Gate-Drain Charge			16.8		nC
I _{SD}	Source-Drain Current (Body Diode)				80	Α
V _{SD}	Forward on Voltage (Note 3)	V _{GS} =0V, I _S =-20A			-1.2	V
t _{rr}	Reverse Recovery Time	I _F =-20A, di/dt=100A/μs		49		ns
Qrr	Reverse Recovery Charge	I _F =-20A, di/dt=100A/μs		69		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature. Notes 2.E_{AS} condition: T_J =25 °C, V_{DD} =40V, V_G =-10V, Rg=25 Ω , L=0.5mH.

Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.



Typical Performance Characteristics

Figure 1. Output Characteristics

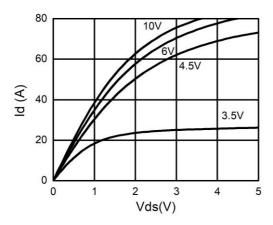


Figure 3. Power Dissipation

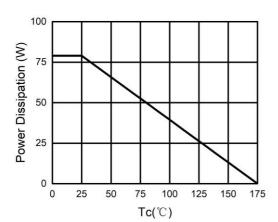


Figure 5. BV_{DSS} vs Junction Temperature

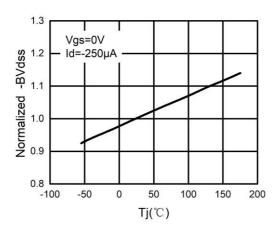


Figure 2. Transfer Characteristics

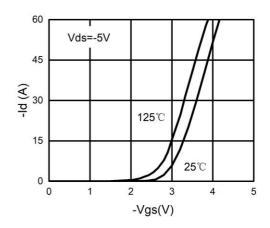


Figure 4. Drain Current

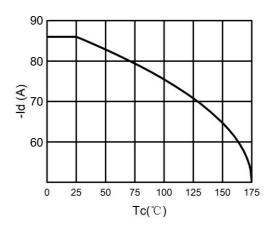
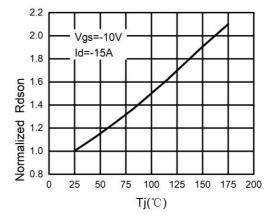


Figure 6. R_{DS(ON)} vs Junction Temperature



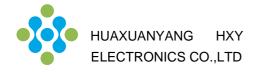


Figure 7. Gate Charge Waveforms

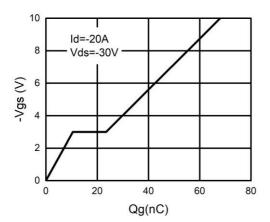


Figure 8. Capacitance

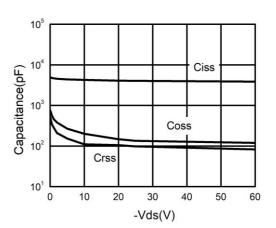


Figure 9. Body-Diode Characteristics

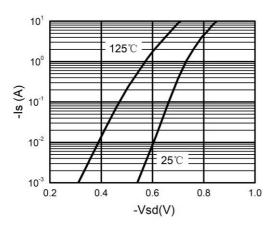
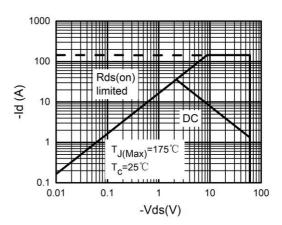
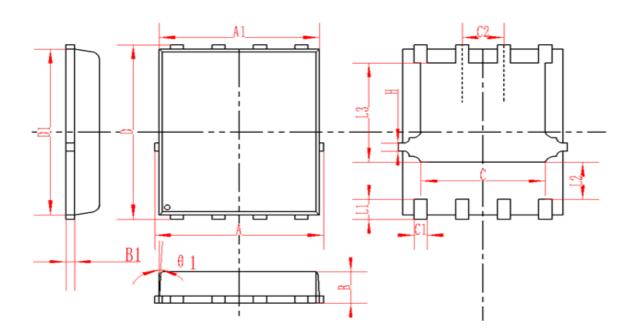


Figure 10. Maximum Safe Operating Area



DFN5X6-8L Package Information



SYMBOL	MM		INCH			
	MIN	NOM	MAX	MIN	NOM	MAX
А	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
В	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF		0.010REF			
С	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2		1.27TYP			0.5TYP	
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
Н	0.24	0.25	0.26	0.009	0.010	0.010



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